## Controlled Normal and Inverse Current-Induced Magnetization Switching and Magnetoresistance in Magnetic Nanopillars

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By combining pairs of ferromagnetic metals with the same or different signs of scattering anisotropies in ferromagnetic-nonmagnetic-ferromagnetic metal nanopillars, we independently invert just the magnetoresistance, just the direction of current-induced magnetization switching, or both together, at room temperature (295 K) and at 4.2 K. In all cases studied, the switching direction is correctly predicted from the net scattering anisotropy of the fixed ferromagnet, including both bulk and interfacial contributions.

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The magnetization of a ferromagnetic (F) metal can be reversed by spin transfer from a spin-polarized current, i.e., without using a magnetic field [1–3]. Such currentinduced magnetization switching (CIMS) [1–20] is seen in (F1-N-F2) nanopillars where a spin-polarized current prepared with a thicker layer F1 passes through a nonmagnetic metal (N) and switches the moment of a thinner layer F2. CIMS is promising for switching small magnetic devices (e.g., magnetic random-access memory), and also raises subtle fundamental issues.

Although CIMS is expected to result from spin polarization of the current, it has yet to be shown that CIMS can be manipulated (e.g., inverted) by changing that polarization. In prior studies, minority electrons were scattered more strongly in F1, F2 and at F1-N and N-F2 interfaces (positive spin anisotropy). The current is then positively spin polarized in the F layers, i.e., carried mainly by majority electrons. In such "standard" conditions, electrons flowing from F1 to F2 (negative charge current, I < 0) switch the moment M2 of F2 from antiparallel (AP) to M1 (high resistance R) to parallel (P) to M1 (low R). Conversely, positive I (>0) switches F2 from P to AP. We call these behaviors "normal" CIMS and normal current-perpendicular-to-plane (CPP) magnetoresistance (MR).

We present CIMS experiments exploiting the possibility of inverting the spin anisotropy by doping F1, F2, or both together, with an impurity (Cr) that scatters majority spin electrons more strongly [21–28]. We thus show, for the first time, that inversion of the spin anisotropy can invert the CIMS direction, i.e., invert the signs of I for AP to P and P to AP transitions. We also find inversions of the MR (larger R for the P state) with appropriately doped samples, as expected from prior CPP-MR results at low temperature [21,22]. Measurements at 295 and 4.2 K show that the qualitative behaviors of both CIMS and MR are independent of temperature over this range.

Analysis of the switching behaviors lets us discriminate between models of CIMS. We divide the standard models of spin-transfer torque (STT) used to describe CIMS into two classes, ballistic [1,2,12] and diffusive [3,4,15,16,19]. Both predict that changing scattering anisotropies can invert the MR and/or CIMS. However, their expectations need not agree. In ballistic transport, the spin anisotropy comes only from reflections at the F-Ninterfaces. Inverting CIMS is predicted to require negative anisotropy at F1-N [12]. Inverting the MR should require opposite scattering anisotropies at F1-N and N-F2 [21]. In diffusive transport, the spin anisotropy of scattering within the F layers is also important, so that one must consider the net anisotropy of each F layer (i.e., the resultant effect of the bulk of F and its F-N interface). An additional effect, spin accumulation, can either support or compete with the effect of polarized current [3,4,15,16,19]. In addition to determining the relation between spin anisotropies and CIMS direction, we answer four questions relevant to understanding CIMS. (a) Is the CIMS direction set only by interface scattering anisotropy? No. (b) Can impurity scattering within the layers be important? Yes. (c) Do the anisotropies of F1and F2 play different roles for the CIMS direction of F2? Yes. (d) Can spin accumulation be important? Yes.

To determine how changing spin anisotropies changes CIMS directions, we combine in different ways three pairs of materials: Py-Cu (Py = Ni<sub>84</sub>Fe<sub>16</sub>), with both bulk and interface anisotropies positive [21]; Fe(Cr)-Cr [Fe(Cr) = Fe<sub>95</sub>Cr<sub>5</sub>], with both negative [22–28]; and Ni(Cr)-Cu [Ni(Cr) = Ni<sub>97</sub>Cr<sub>3</sub>], with thick enough Ni(Cr) so its negative anisotropy dominates the positive anisotropy of the interface [29]. The net anisotropy is found using the MR. Comparing Fe(Cr)-Cr with Ni(Cr)-Cu for F1 or F2 tests the importance of interface anisotropies. Table I lists the signs for F1, F2 bulk, F1-N, N-F2 interfaces, and F1(net), F2(net), as well as for the observed MR and CIMS.

Figure	F1-N-F2	F1	F1-N	F1(Net)	F2	<i>N-F</i> 2	F2(Net)	MR	CIMS
1	Py-Cu-Py	+	+	+	+	+	+	+	+
2	Fe(Cr)-Cr-Fe(Cr)	_	_	_	_	_	_	+	_
3	Py-Cu-Cr-Fe(Cr)	+	+	+	_	_	_	_	+
4	Ni(Cr)-Cu-Py	_	+	_	+	+	+	_	_
5	Py-Cu-Ni(Cr)	+	+	+	_	+	_	_	+

TABLE I. F1-N-F2 for each figure, giving the spin anisotropies (+ = positive, - = negative) of F1, F1-N, and their net anisotropy F1(Net), those of F2, N-F2, and their net anisotropy F2(Net), and the signs of the observed MR and CIMS (+ = normal and - = inverse).

Our sample preparation and measurement techniques are described in Ref. [20]. Our multilayers are triode sputtered onto Si substrates, and patterned into nanopillars of roughly elliptical shape and dimensions  $\sim$ 70 nm  $\times$  130 nm. The samples consist of a thick Cu lower contact, the multilayer, and a thick Au top contact. The N layer is made thick (6-20 nm) to minimize exchange coupling between F1 and F2. To simplify switching, samples are ion milled only through F2 and part of N, leaving F1 (fixed polarizer) to have a much larger area ( $\sim \mu m^2$ ) and be thicker than F2. Dipolar coupling between F1 and F2 is then minimal, and H(along the easy axis) reverses M1 and M2 sequentially, but I reverses only M2 of F2 (free switcher). For each sample, the switching directions of MR and CIMS are the same at 295 and 4.2 K. Each switching behavior was independently reproduced, and no inconsistent switching was seen.

Py and Py-Cu interfaces both have positive scattering anisotropy [21]. In accord with prior data [20], Fig. 1 shows that Py(24)-Cu(10)-Py(6) nanopillars (layer thicknesses in nm) give normal MR and normal CIMS. At both 295 and 4.2 K, the MR transitions from P to AP occur after H passes through zero, consistent with little or no magnetic coupling. The agreement between minimum and maximum values of dV/dI for the MR and CIMS curves shows that the switching is complete. Figures 2–5 also show weak coupling and complete switching.

In contrast to Py and Py-Cu, Fe(Cr) and Fe-Cr interfaces both have negative scattering anisotropies [22–28]. Since F1 and F2 are the same alloy, Fe(Cr)(30)-Cr(6)-Fe(Cr)(3.5) nanopillars should give normal MR [21,22]. Figure 2 shows that they do and also give inverse CIMS; see also [23]. The changes in dV/dI vs I or H are smaller than for Py-Cu-Py, due to spin-memory loss in the Cr(6) layer [24] and smaller scattering anisotropy of Fe(Cr) [22].

Figure 3 shows data for the four component system Py(20)-Cu(7)-Cr(3)-Fe(Cr)(3). Combining net positive anisotropy for F1 with net negative for F2 gives the expected inverse MR [21,22]. But the CIMS is normal—I > 0 switches from P to AP—since inverse MR means the largest resistance in the P state.

Figure 4 shows the fourth case, Ni(Cr)(20)-Cu(20)-Py(10). Combining net negative anisotropy for Ni(Cr) 157203-2 with net positive anisotropy for Py gives the expected inverse MR, and now inverse CIMS.

Figure 5 shows another way to achieve inverse MR with normal CIMS, using Py(24)-Cu(10)-NiCr(4). In Figs. 3 and 5, this same combination of MR and CIMS occurs with opposite F2 interface anisotropies—negative in Fig. 3 but positive in Fig. 5.

Last, in Figs. 2 and 4, opposite interface anisotropies for F1 do not change the CIMS direction.

Before comparing our data with theory, we summarize the results in Figs. 1–5. As expected for the MR [21,22], when the net scattering anisotropies for F1 and F2 are the same (Figs. 1 and 2), the MR is normal, and when they are opposite (Figs. 3–5), the MR is inverse. New for CIMS, when the net scattering anisotropy for F1 is positive, CIMS is normal (Figs. 1, 3, and 5), and when it is negative (Figs. 2 and 4), CIMS is inverse. For these samples, the direction of CIMS is set by the net scattering anisotropy of F1 and is independent of that of F2. Comparing Figs. 3 and 5, and Figs. 2 and 4, shows that, when bulk scattering

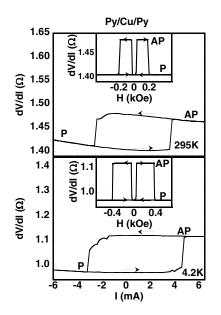


FIG. 1. Py(24)-Cu(10)-Py(6) data at 295 K (top) and 4.2 K (bottom) showing normal MR (dV/dI vs H at I = 0) in the insets and normal CIMS for dV/dI vs I in the main figures at H = 0 Oe for 295 K and at H = 20 Oe for 4.2 K. In all figures, I > 0 is always from F1 to F2.

Fe(Cr)/Cr/Fe(Cr)

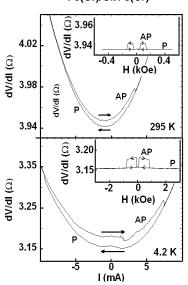


FIG. 2. Fe(Cr)(30)-Cr(6)-Fe(Cr)(3.5) data at 295 K (top) and 4.2 K (bottom) showing normal MR (dV/dI vs H at I = 0) in the insets but inverse CIMS for dV/dI vs I at H = 0 in the main figures.

predominates, the CIMS direction is independent of the scattering anisotropy of F1-N and N-F2. Finally, dominance of the bulk contribution of scattering anisotropy in either F1 [e.g., Ni(Cr) in Fig. 4] or F2 [Ni(Cr) in Fig. 5] is inconsistent with ballistic transport through the nanopillar, where the interfaces must dominate the scattering. While ballistic STT models cannot describe our data involving Ni(Cr), the CIMS directions in Figs. 1–5 accord

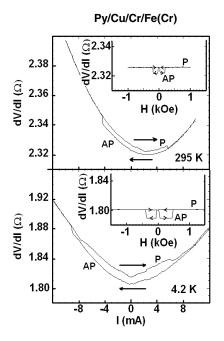


FIG. 3. Py(20)-Cu(7)-Cr(3)-Fe(Cr)(3) data at 295 K (top) and 4.2 K (bottom) showing inverse MR (dV/dI vs H at I = 0) in the insets but normal CIMS for dV/dI vs I at H = 0 in the main figures.

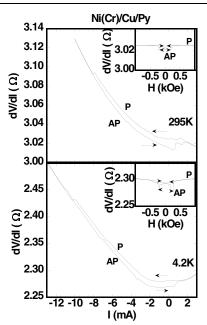


FIG. 4. Ni(Cr)(20)-Cu(20)-Py(10) data at 295 K (top) and 4.2 K (bottom) showing inverse MR (dV/dI vs H at I = 0) in the insets and inverse CIMS for dV/dI vs I at H = 0 in the main figures.

with the ballistic prediction of [12] if the scattering anisotropy at the F1-N interface is simply replaced by the net anisotropy for F1.

For diffusive transport, the current polarization in N depends upon the net scattering anisotropies of both F1 and F2, and CIMS depends upon both the spin-polarized charge current and spin-accumulation effects [3,4,15,19]. Equation (1) reproduces Eq. 5 of Ref. [19] for the torque  $\Gamma^{P}$  at a small angle from the P state (for  $\Gamma^{AP}$ , replace P by AP). Our notations for F1 and F2 are reversed from [19].

$$\Gamma^{\rm P}/\hbar = [\{(\nu_F m_N^{\rm P})/8 + (j_{m,N}^{\rm P})/2\}(1 - e^{-t_N/\lambda_N}) + \{(\nu_F m_{F1}^{\rm P})/4 + j_{m,F1}^{\rm P}\}e^{-t_N/\lambda_N}] \times [\hat{M}_2 \times (\hat{M}_2 \times \hat{M}_1)].$$
(1)

Equation (1) comes from an extension of the Valet-Fert

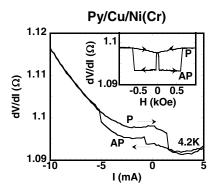


FIG. 5. Py(24)-Cu(10)-Ni(Cr)(4) data at 4.2 K showing inverse MR (dV/dI vs H at I = 0) in the inset and normal CIMS for dV/dI at H = 0 Oe in the main figure.

[30] model of CPP-MR to noncollinear states.  $\nu_F$  is the Fermi velocity in N,  $m_N^P$  and  $j_{m,N}^P$  are the spinaccumulation density [15,16,19,30] and spin-current density in N just outside the F2-N interface calculated for the P state,  $m_{F1}^P$  and  $j_{m,F1}^P$  are the same quantities in F1 just inside the F1-N interface,  $t_N$  and  $\lambda_N$  are the thickness and mean-free path of N, and  $\hat{M}$  is a unit vector in the direction of **M**. The second set of {} braces dominates the usual case when  $t_N \ll \lambda_N$  and the first dominates if  $t_N \gg \lambda_N$ . The signs of spin current and spin accumulation can support each other or compete.

Using the best parameters from CPP-MR experiments [21,24,29], we calculate spin currents and spin accumulations [21,30], and insert them into  $\Gamma^{\rm P}$  or  $\Gamma^{\rm AP}$ . Except for Fig. 4, the signs of spin current and accumulation always agree and are as expected from the sign of the net spin anisotropy of F1 seen by MR. The case for Fig. 4 is more complex. For P to AP, the spin accumulation dominates  $\Gamma^{\rm P}$  and gives the observed inverse CIMS at I < 0; due to the particular parameters of Ni(Cr) and Py, the spin current alone would predict normal CIMS. For AP to P, the spin current dominates  $\Gamma^{\rm AP}$  and gives the observed inverse CIMS at I > 0. Thus, we reproduce the behaviors in Fig. 4.

To summarize, we have shown that judiciously chosen pairs of ferromagnetic metals or alloys can produce all four combinations of normal and inverse MR and currentinduced magnetization switching at both 4.2 and 295 K. The MR is normal if the net scattering anisotropies of F1 and F2 have the same sign, and inverse if they do not. For the samples studied, the CIMS direction is set solely by the net anisotropy for F1, although in Fig. 4 this result requires dominance of spin accumulation for the P to AP transition. This latter result, as well as the inverted MRs in Figs. 4 and 5, show that the interpretation of MR and CIMS must generally take account not only of the interface scattering assumed in ballistic models but also the scattering (and diffusion) within the F layers. As the widely accepted mechanism of CIMS is a quasiinterfacial absorption of the transverse component of the spin current [1,12,15,19], the importance of scattering within the F layers might seem surprising. However, in a noncollinear magnetic configuration, the transverse spin current in the frame of F2 is related to the longitudinal one in F1, and a global treatment [15,19] of the longitudinal and transverse components of the spin current and spin accumulation requires the diffusive aspects of the CPP-MR theory [21,30].

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